

## Description

The SX4955A uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

## General Features

$V_{DS} = -30V$   $I_D = 8.3A$

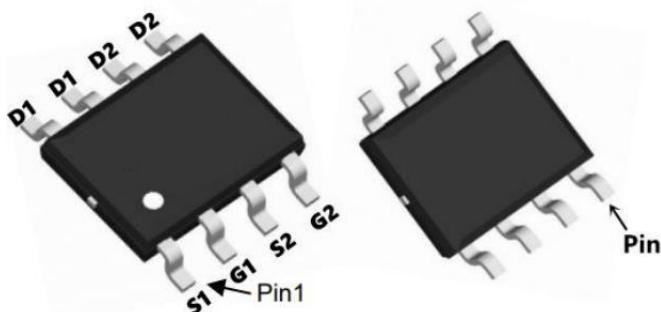
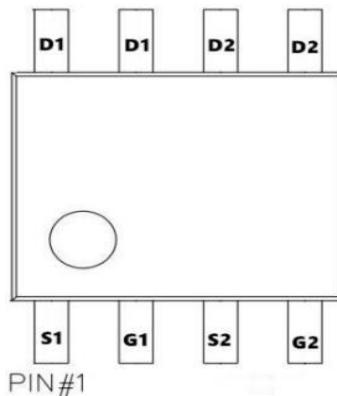
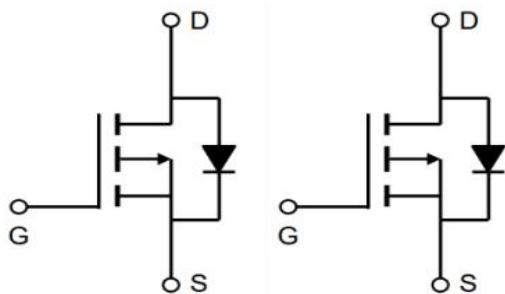
$R_{DS(ON)} < 22m\Omega$  @  $V_{GS}=10V$

## Application

Lithium battery protection

Wireless impact

Mobile phone fast charging



## Absolute Maximum Ratings ( $T_c=25^\circ C$ unless otherwise noted)

Symbol	Parameter	Rating	Units
VDS	Drain-Source Voltage	-30	V
VGS	Gate-Source Voltage	$\pm 20$	V
ID@ $T_c=25^\circ C$	Continuous Drain Current, VGS @ -10V1	-8.3	A
ID@ $T_c=100^\circ C$	Continuous Drain Current, VGS @ -10V1	-6.8	A
IDM	Pulsed Drain Current2	-30	A
EAS	Single Pulse Avalanche Energy3	125	mJ
PD@ $T_c=25^\circ C$	Total Power Dissipation4	1.47	W
TSTG	Storage Temperature Range	-55 to 150	°C
TJ	Operating Junction Temperature Range	-55 to 150	°C
R <sub>θJA</sub>	Thermal Resistance Junction-Ambient 1	85	°C/W
R <sub>θJC</sub>	Thermal Resistance Junction-Case1	3.6	°C/W

**Electrical Characteristics ( $T_J=25^\circ\text{C}$ , unless otherwise noted)**

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
V(BR)DSS	Drain-Source Breakdown Voltage	$V_{GS}=0\text{V}$ , $I_D=-250\mu\text{A}$	-30	-33	-	V
IDSS	Zero Gate Voltage Drain Current	$V_{DS}=-30\text{V}$ , $V_{GS}=0\text{V}$ ,	-	-	-1	$\mu\text{A}$
IGSS	Gate to Body Leakage Current	$V_{DS}=0\text{V}$ , $V_{GS}=\pm 20\text{V}$	-	-	$\pm 100$	nA
VGS(th)	Gate Threshold Voltage	$V_{DS}=V_{GS}$ , $I_D=-250\mu\text{A}$	-1.2	-1.5	-2.5	V
RDS(on)	Static Drain-Source on-Resistance note3	$V_{GS}=-10\text{V}$ , $I_D=-10\text{A}$	-	16	22	$\text{m}\Omega$
		$V_{GS}=-4.5\text{V}$ , $I_D=-5\text{A}$	-	25	30	
Ciss	Input Capacitance	$V_{DS}=-15\text{V}$ , $V_{GS}=0\text{V}$ , $f=1.0\text{MHz}$	-	1250	-	pF
Coss	Output Capacitance		-	327	-	pF
Crss	Reverse Transfer Capacitance		-	278	-	pF
Qg	Total Gate Charge	$V_{DS}=-15\text{V}$ , $I_D=-9.1\text{A}$ , $V_{GS}=-10\text{V}$	-	30	-	nC
Qgs	Gate-Source Charge		-	5.3	-	nC
Qgd	Gate-Drain("Miller") Charge		-	7.6	-	nC
td(on)	Turn-on Delay Time		-	14	-	ns
tr	Turn-on Rise Time		-	20	-	ns
td(off)	Turn-off Delay Time	$V_{DD}=-15\text{V}$ , $I_D=-6\text{A}$ , $V_{GS}=-10\text{V}$ , $R_{GEN}=2.5\Omega$	-	95	-	ns
tf	Turn-off Fall Time		-	65	-	ns
IS	Maximum Continuous Drain to Source Diode Forward Current		-	-	-10	A
ISM	Maximum Pulsed Drain to Source Diode Forward Current		-	-	-40	A
VSD	Drain to Source Diode Forward Voltage	$V_{GS}=0\text{V}$ , $I_S=-11\text{A}$	-	-0.8	-1.2	V

**Note :**

- 1、The data tested by surface mounted on a 1 inch 2 FR-4 board with 2OZ copper.
- 2、The data tested by pulsed , pulse width  $\leq 300\mu\text{s}$  , duty cycle  $\leq 2\%$
- 3、The EAS data shows Max. rating . The test condition is  $VDD=-25\text{V}$ , $VGS=-10\text{V}$ , $L=0.1\text{mH}$ , $IAS=-23\text{A}$
- 4、The power dissipation is limited by  $150^\circ\text{C}$ junction temperature
- 5、The data is theoretically the same as ID and IDM , in real applications , should be limited by total power dissipation.

## Typical Characteristics

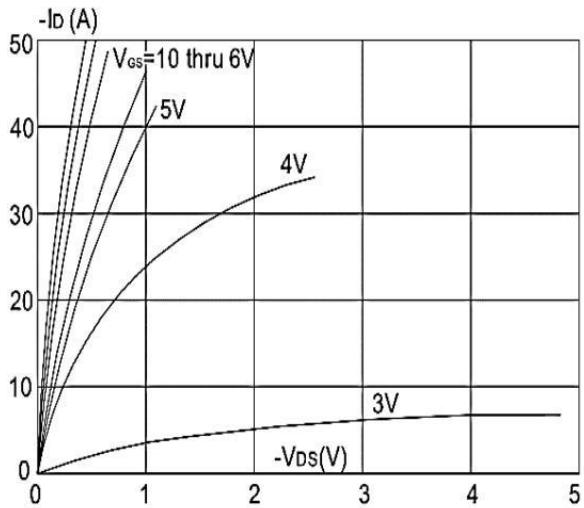


Figure 1: Output Characteristics

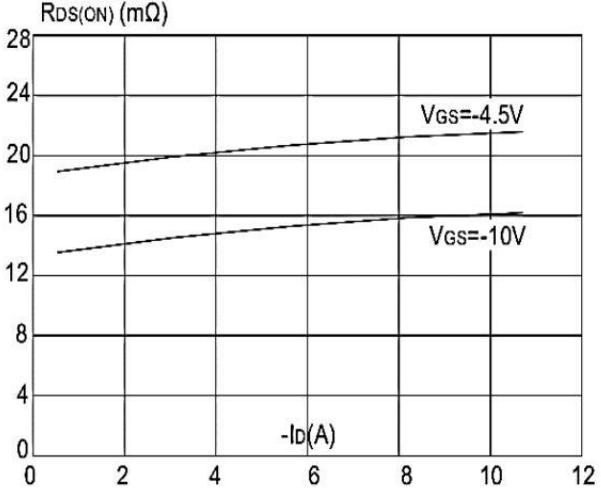


Figure 3: On-resistance vs. Drain Current

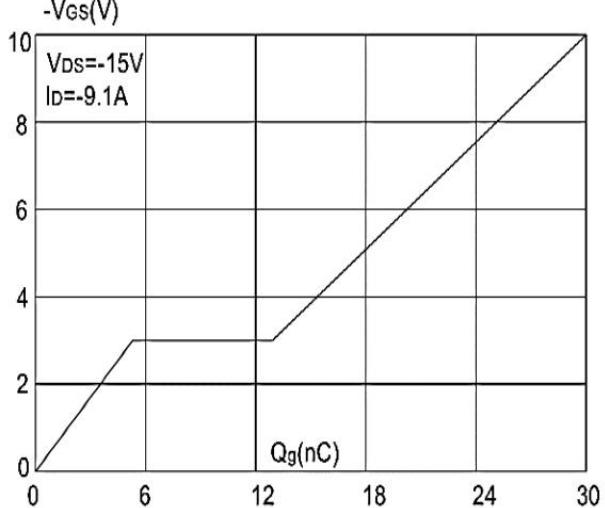


Figure 5: Gate Charge Characteristics

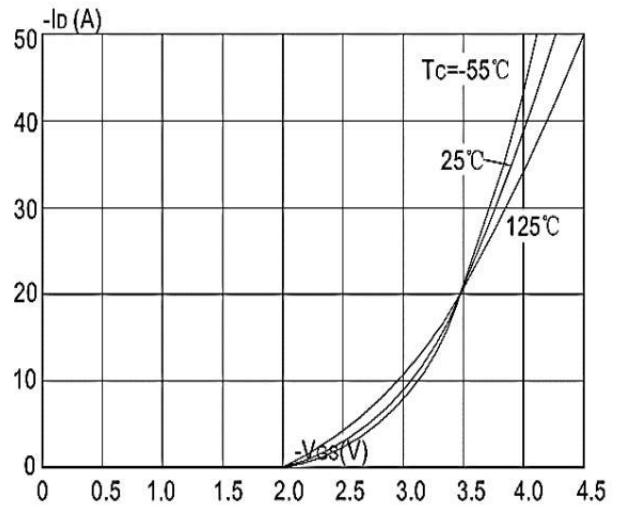


Figure 2: Typical Transfer Characteristics

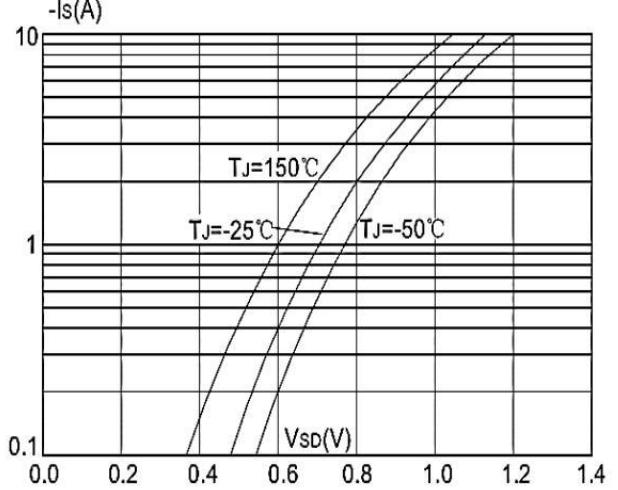


Figure 4: Body Diode Characteristics

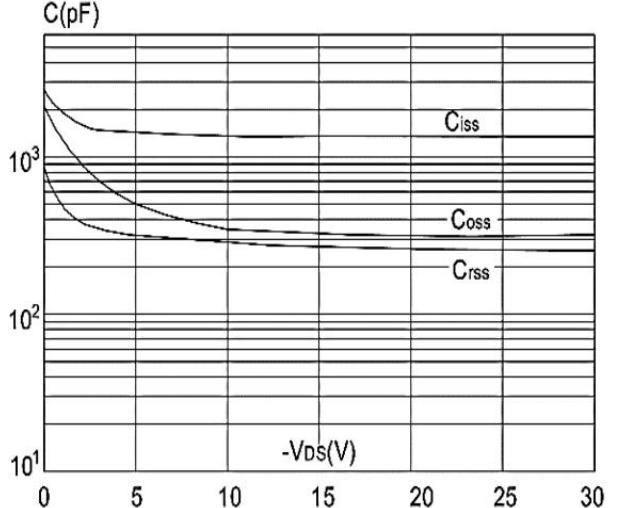


Figure 6: Capacitance Characteristics

## Typical Characteristics

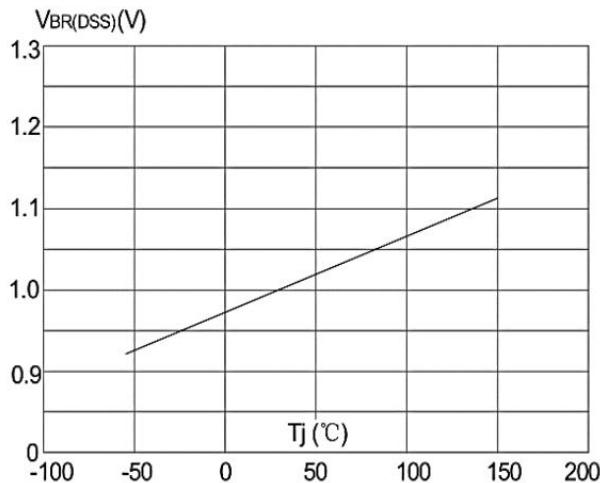


Figure 7: Normalized Breakdown Voltage vs.  
Junction Temperature

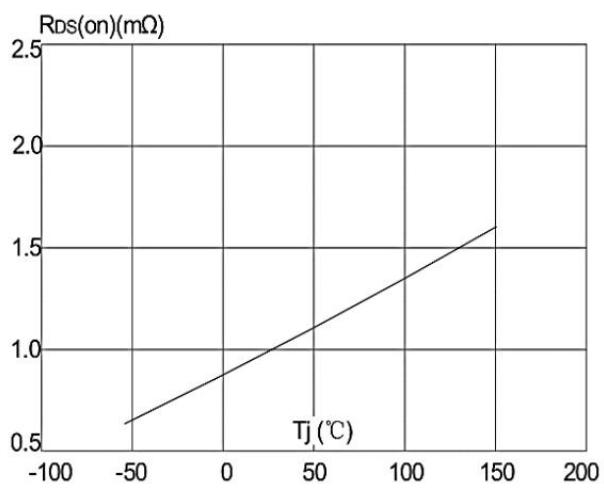


Figure 8: Normalized on Resistance vs.  
Junction Temperature

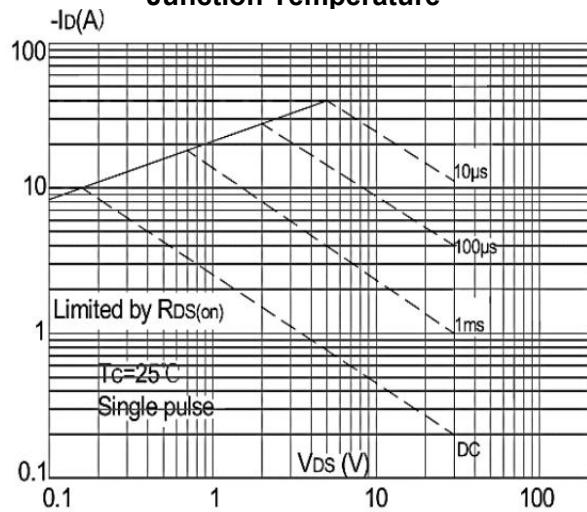


Figure 9: Maximum Safe Operating Area

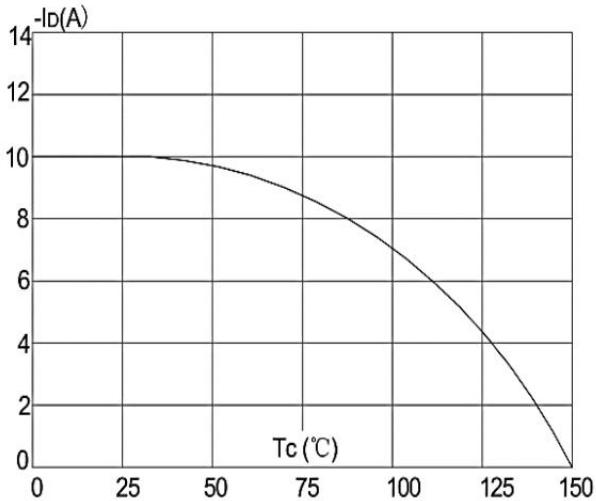


Figure 10: Maximum Continuous Drain Current  
vs. Ambient Temperature

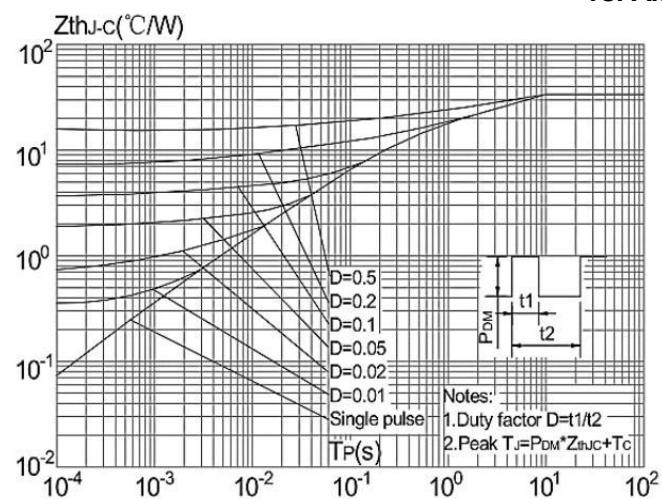
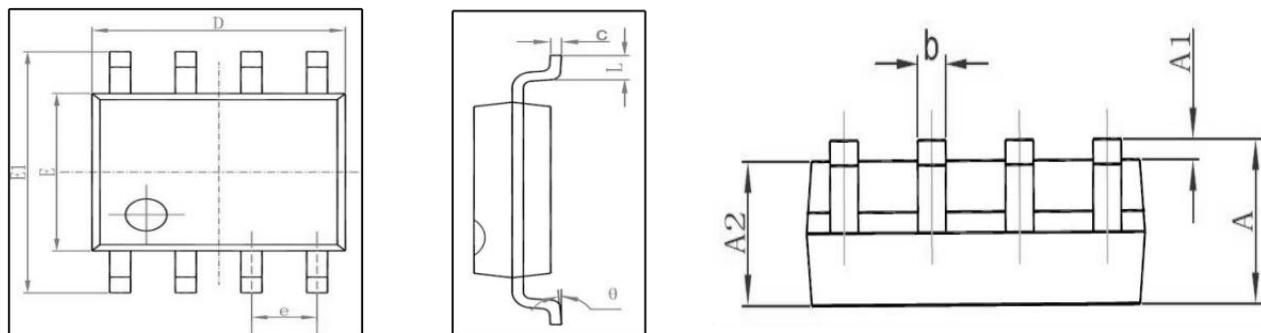
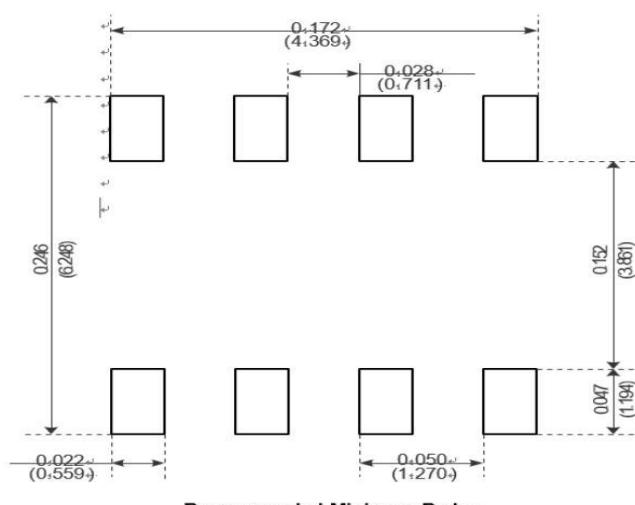


Figure 11: Maximum Effective  
Transient Thermal Impedance, Junction-to-Ambient

## Package Mechanical Data-SOP-8L



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270 (BSC)		0.050 (BSC)	
L	0.400	1.270	0.016	0.050
$\theta$	0°	8°	0°	8°



### Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
TAPING	SOP-8L		3000